

V_{DSS} , -30V $R_{DS(ON)}$, 9.5m Ω (max.) @ $V_{GS}=-10V$ $R_{DS(ON)}$, 15m Ω (max.) @ $V_{GS}=-4.5V$ I_D , -39 A	PDFN 3.3x3.3-8L		

Description	Features
The SGP3008E uses advanced Trench technology and designs to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.	<ul style="list-style-type: none"> • Low On-Resistance • Low Input Capacitance • Low Miller Charge • Low Input / Output Leakage • Pb-free lead plating; RoHS compliant
	Applications
	<ul style="list-style-type: none"> • Lithium-Ion Secondary Batteries • Load Switch • DC-DC converters and Off-line UPS

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SGP3008E	Halogen-Free	PDFN 3.3x3.3-8L	E	Tape & Reel	5,000

Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	$T_C=25^{\circ}C$	-39
		$T_C=100^{\circ}C$	-25
Drain Current-Pulsed ^{Note 1}	I_{DM}	-67	A
Avalanche Current, L=0.1mH	I_{AS}	-30	A
Avalanche Energy, L=0.1mH	E_{AS}	45	mJ
Maximum Power Dissipation	P_D	$T_C=25^{\circ}C$	20.8
		$T_C=100^{\circ}C$	8.3
Storage Temperature Range	T_{STG}	-55 to +150	$^{\circ}C$
Operating Junction Temperature Range	T_J	-55 to +150	$^{\circ}C$

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Thermal resistance, Junction-to-Ambient ^{Note 2}	$R_{\theta JA}$	Steady State	-	59.2	80	$^{\circ}C/W$
Thermal resistance, Junction-to-Case ^{Note 2}	$R_{\theta JC}$	Steady State	-	6	8	$^{\circ}C/W$

Electrical Characteristics (T_J=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =-250μA	-30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =-250μA	-1.0	-	-2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _{DS} =-15A	-	-	9.5	mΩ
		V _{GS} =-4.5V, I _{DS} =-8A	-	-	15	mΩ

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V, f=1MHz	-	3875	-	pF
Output Capacitance	C _{oss}		-	398	-	
Reverse Transfer Capacitance	C _{rss}		-	278	-	
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz	-	2.89	-	Ω

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Turn-On Delay Time	T _{d(on)}	V _{DD} =-15V, V _{GS} =-10V, R _G =3Ω, I _D =-20A	-	13.9	-	ns
Rise Time	t _r		-	64.1	-	
Turn-Off Delay Time	T _{d(off)}		-	51.8	-	
Fall Time	t _f		-	53.1	-	
Total Gate Charge	Q _g	V _{DS} =-15V, V _{GS} =-10V, I _D =-20A	-	63.5	-	nC
Gate to Source Gate Charge	Q _{gs}		-	14.7	-	
Gate to Drain "Miller" Charge	Q _{gd}		-	8.83	-	

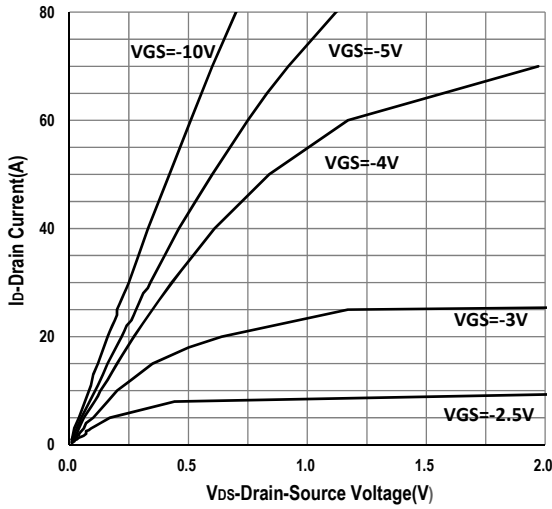
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-1A	-	-	-1.2	V
Body Diode Reverse Recovery Time	t _{rr}	V _{DD} =-24V, I _F =-20A, di/dt=100A/μs	-	23.0	-	ns
Body Diode Reverse Recovery Charge	Q _{rr}	V _{DD} =-24V, I _F =-20A, di/dt=100A/μs	-	16.0	-	nC
Reverse Recovery Current	I _{RRM}	V _{DD} =-24V, I _F =-20A, di/dt=100A/μs	-	1.27	-	A

Notes:

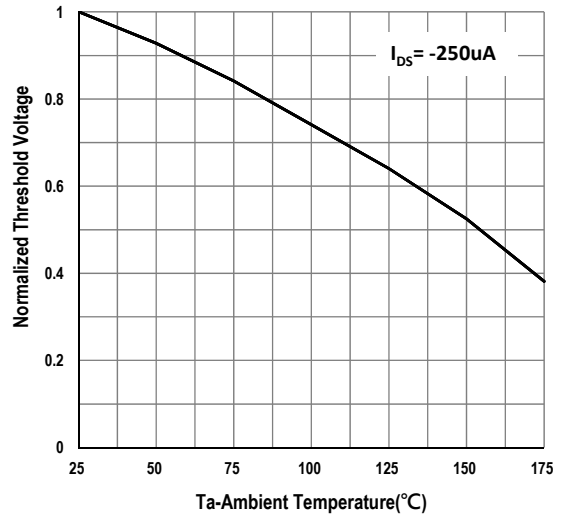
1. Pulse Test: Pulse Width ≤ 10ms, Duty Cycle ≤ 1%.
2. For surface-mounted devices, both R_{θJA} and R_{θJC} are measured with the device mounted on approximately 1"×1" FR-4 PCBs. In actual applications, many factors including the PCB material and layout, may affect the thermal resistance of the device-board assembly. For best results, characterize the thermal resistance directly in the application circuit.

Typical Operating Characteristics

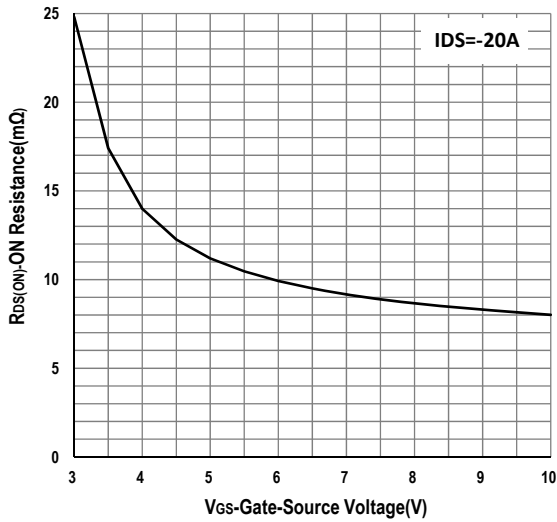
Output Characteristics



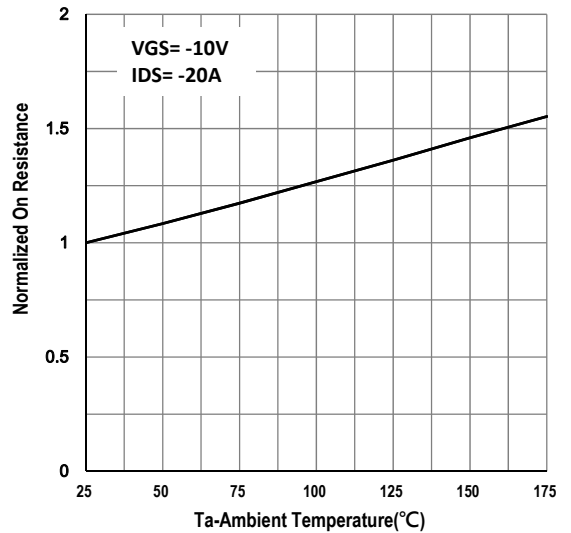
Gate Threshold Voltage



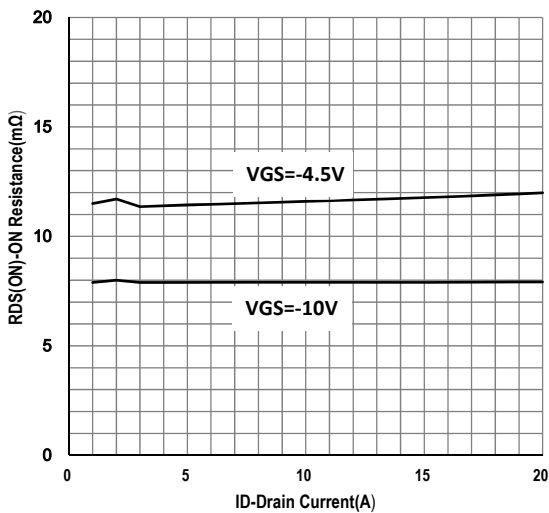
Gate-Source On Resistance



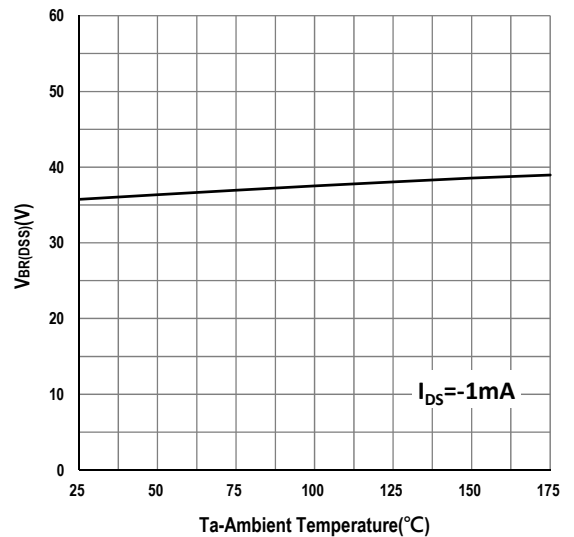
Drain-Source On Resistance



Drain-Source On Resistance

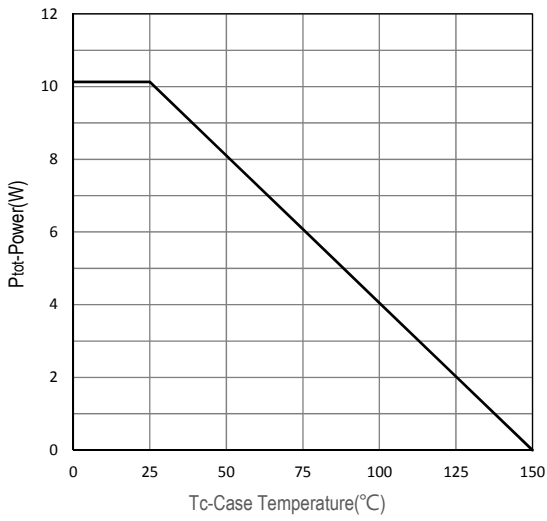


Source-Drain Diode Forward

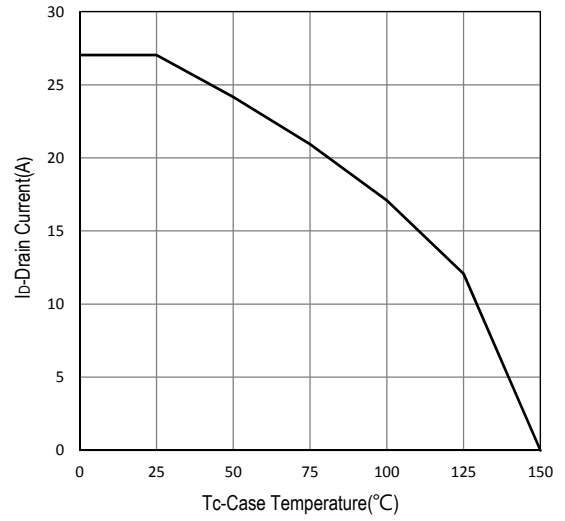


Typical Operating Characteristics (Cont.)

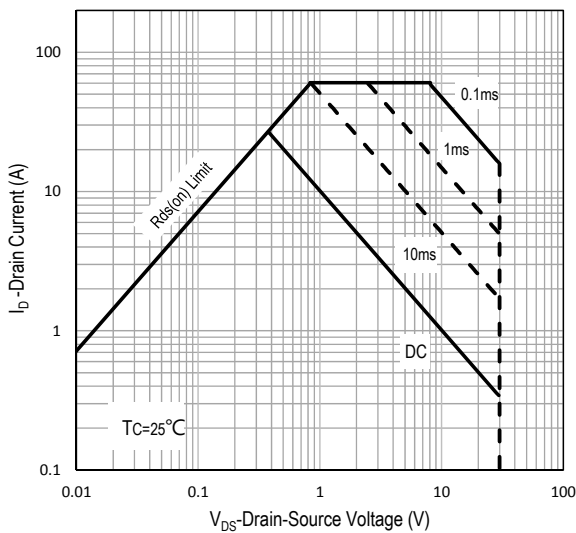
Power Dissipation



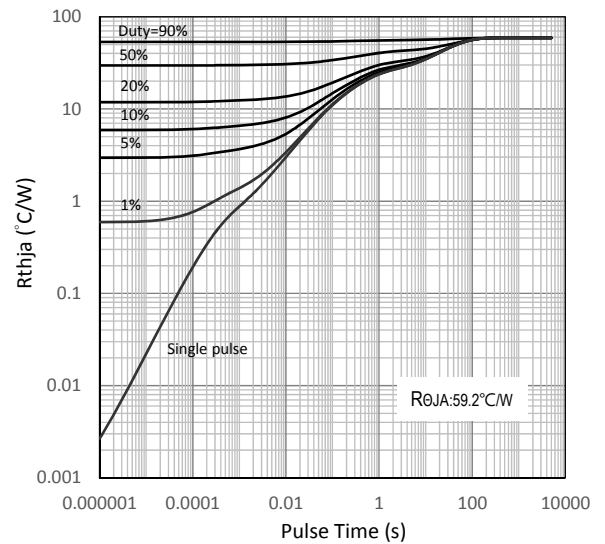
Drain Current



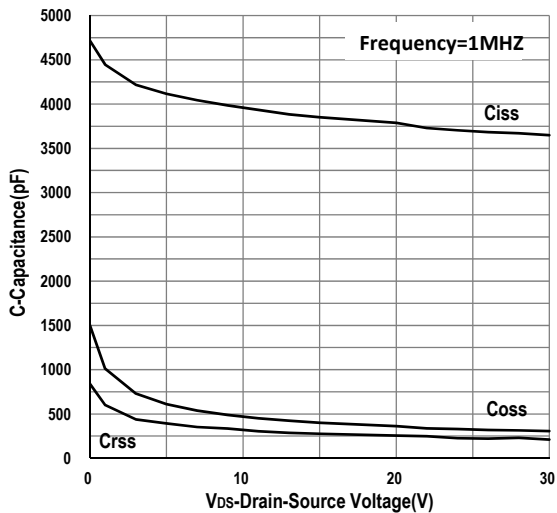
Safe Operation Area



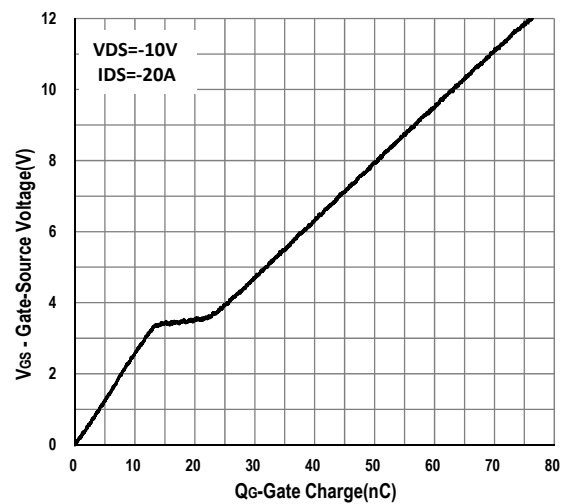
Transient Thermal Impedance




Capacitance



Gate Charge



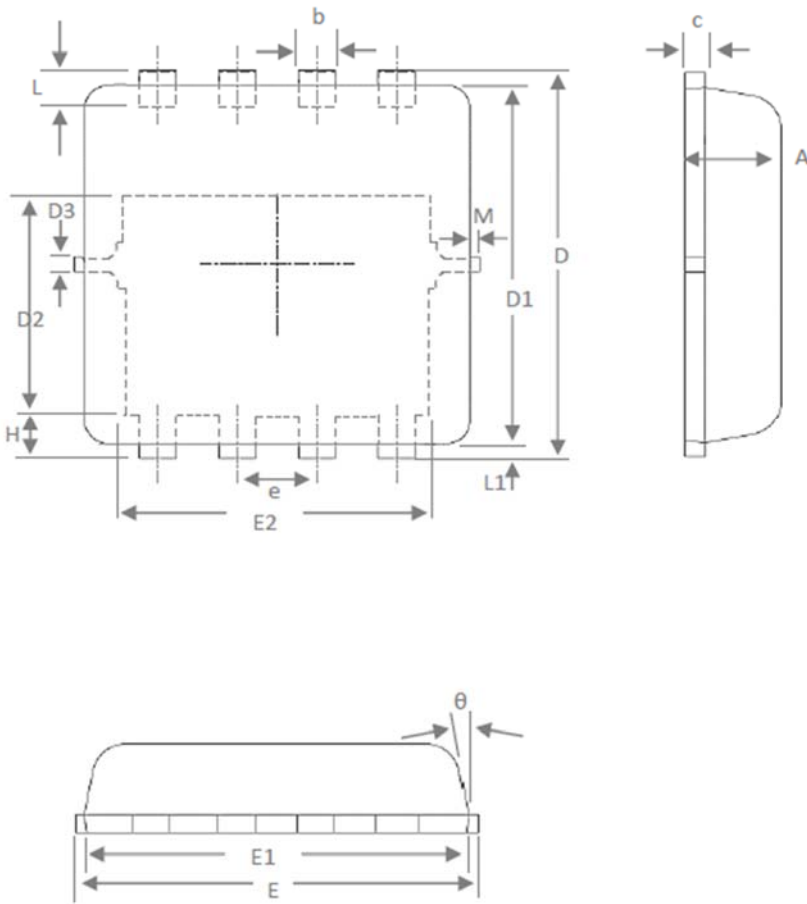
Marking Information

PDFN 3.3x3.3-8L (E)	Marking Rule
<p data-bbox="124 369 293 403">Laser Marking</p> 	<p data-bbox="807 369 1070 403"><u>Line 1</u> : Device Name</p> <p data-bbox="807 416 903 450">P3008E</p> <p data-bbox="807 501 1038 535"><u>Line 2</u> : Date Code</p> <p data-bbox="807 548 922 582">YMMXXX</p> <p data-bbox="807 633 983 667">Y : Year Code</p> <p data-bbox="807 680 1027 714">MM : Month Code</p> <p data-bbox="807 728 1062 761">XXX : Serial Number</p> <p data-bbox="807 813 1190 846">Year Code Description As Below</p>

Year Code Description

Year Code	Year	
0	2010	2020
1	2011	2021
2	2012	2022
3	2013	2023
4	2014	2024
5	2015	2025
6	2016	2026
7	2017	2027
8	2018	2028
9	2019	2029

Package of Dimension

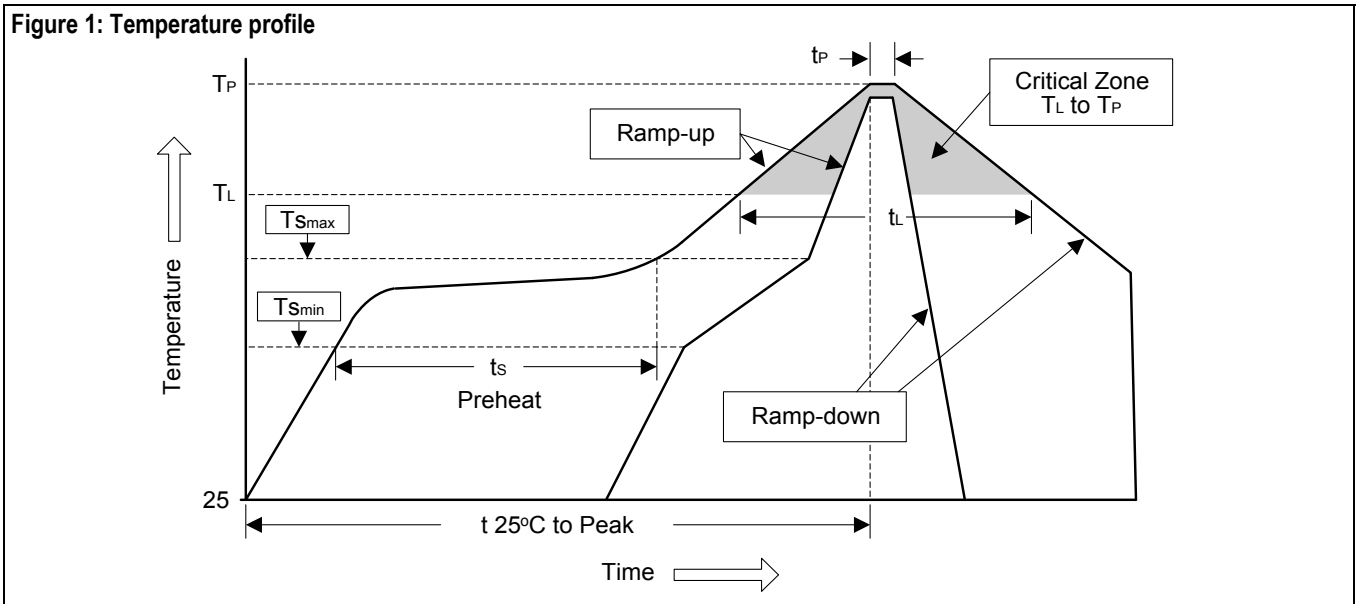


Symbol	Min	Nor	Max
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	-	0.13	-
E	3.00	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
θ	-	10°	12°
M	-	-	0.15

Soldering Methods for Silicongear's Products

1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T_{smin})	100°C	150°C
- Temperature Max (T_{smax})	150°C	200°C
- Time (min to max) (t_s)	60 to 120 sec	60 to 180 sec
T_{smax} to T_L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T_L)	183°C	217°C
- Time (t_L)	60 to 150 sec	60 to 150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec

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